

Therefore, the Examiner is respectfully requested to withdraw the §102 rejection of claim 1.

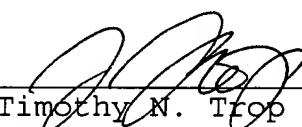
Claim 33 calls for defining an opening in a masking layer over semiconductor structure and causing impurities to enter a portion of said structure through the opening to enhance the oxidation of said structure beyond that which would be expected from the crystallographic damage effects. Therefore, for the same reasons, the §102 rejection of claim 33 is also inappropriate and should be withdrawn.

Moreover, claim 33 calls for using said mask to form a trench through the portion of said structure containing said impurities. Thus, claim 33 calls for using the same mask to implant the oxidation enhancing impurities and to subsequently form the trench. This is no where suggested in Hong or in any of the art relied upon to support the taking of official notice.

In view of these remarks, reconsideration of the rejection is respectfully requested.

Respectfully submitted,

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